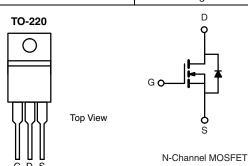


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Vishay Siliconix

# Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.009			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.013			
I <sub>D</sub> (A)	50			
Configuration	Single			



#### **FEATURES**

- TrenchFET® Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested
- AEC-Q101 Qualifiedd
- Material categorization:
  For definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>



ORDERING INFORMATION			
Package	TO-220		
Lead (Pb)-free and Halogen-free	SQP50N06-09L-GE3		

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unles		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	60	V
Gate-Source Voltage	V <sub>GS</sub>	± 20	V	
Continuous Drain Current	T <sub>C</sub> = 25 °C <sup>a</sup>	- I <sub>D</sub>	50	
Continuous Drain Current	T <sub>C</sub> = 125 °C		49	
Continuous Source Current (Diode Conduct	I <sub>S</sub>	50	А	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>		200
Single Pulse Avalanche Current	0.4	I <sub>AS</sub>	48	
Single Pulse Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	115	mJ
Maximum Dawar Dissinationh	T <sub>C</sub> = 25 °C	D	136	W
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C	$P_{D}$	45	VV
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	50	°C/W	
Junction-to-Case (Drain)		R <sub>thJC</sub>	1.1	]	

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static	1					L		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		60	-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	· V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.5	2.0	2.5	v	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nΑ	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V	-	-	1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	-	-	250	·	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A	-	0.0071	0.0090		
Drain Course On State Besistance	В	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C	-	-	0.0160	0	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C	-	-	0.0190	Ω	
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 10 A	-	0.0094	0.0130		
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		-	62	-	S	
Dynamic <sup>b</sup>					•			
Input Capacitance	C <sub>iss</sub>			-	2451	3065	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	435	545		
Reverse Transfer Capacitance	C <sub>rss</sub>	1		-	192	240		
Total Gate Charge <sup>c</sup>	Qg			-	48	72		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 50 \text{ A}$	-	7.1	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	13.5	-		
Gate Resistance	R <sub>g</sub>	f = 1 MHz		0.85	1.7	2.6	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	$V_{DD} = 30 \text{ V, } R_L = 0.6 \Omega$ $I_D \cong 50 \text{ A, } V_{GEN} = 10 \text{ V, } R_g = 1 \Omega$		-	10	15		
Rise Time <sup>c</sup>	t <sub>r</sub>			-	11	17	- ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	27	41		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	8	12		
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>	•						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	200	Α	
Forward Voltage	$V_{SD}$	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V			0.82	1.5	V	

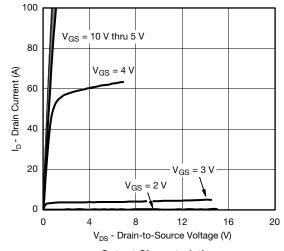
### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

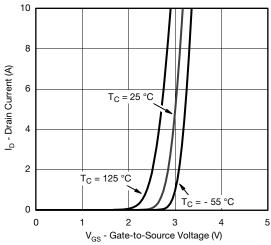
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



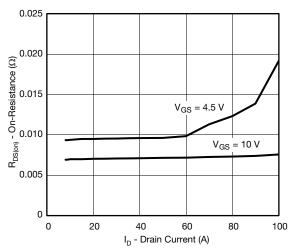
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



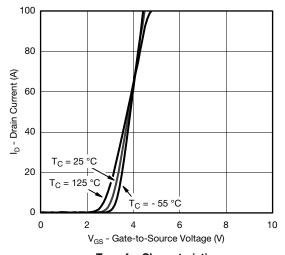
## **Output Characteristics**



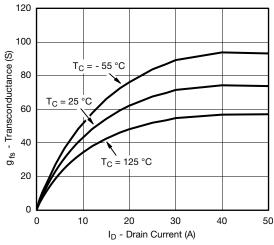
#### **Transfer Characteristics**



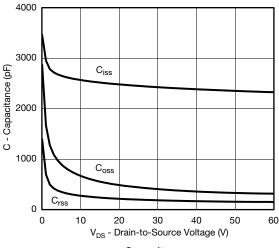
**On-Resistance vs. Drain Current** 



**Transfer Characteristics** 



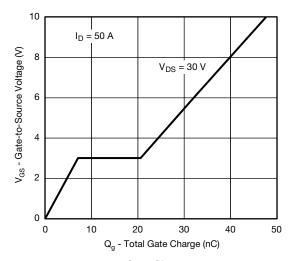
Transconductance



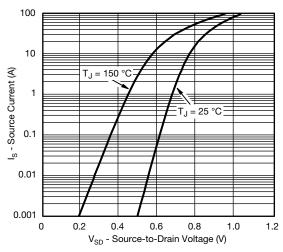
Capacitance



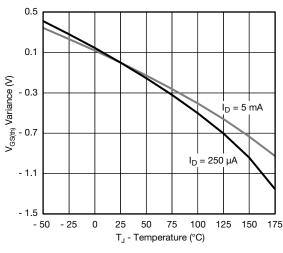
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



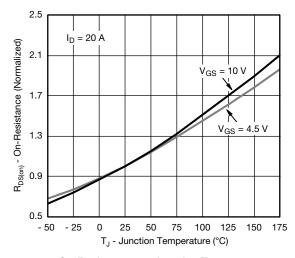
#### **Gate Charge**



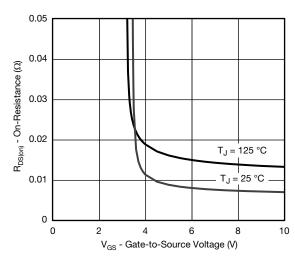
## Source Drain Diode Forward Voltage



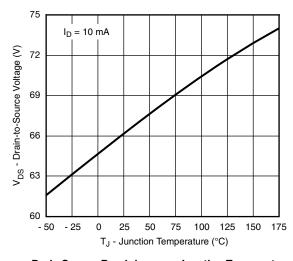
**Threshold Voltage** 



### On-Resistance vs. Junction Temperature



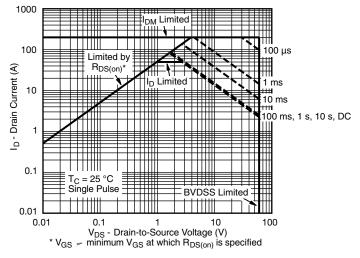
On-Resistance vs. Gate-to-Source Voltage



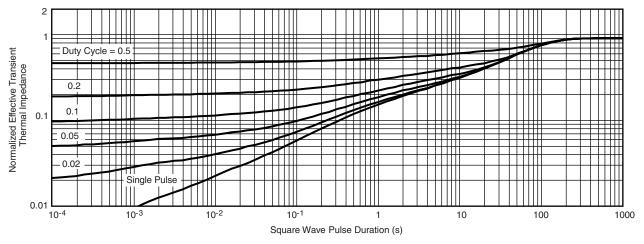
Drain Source Breakdown vs. Junction Temperature



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



Safe Operating Area

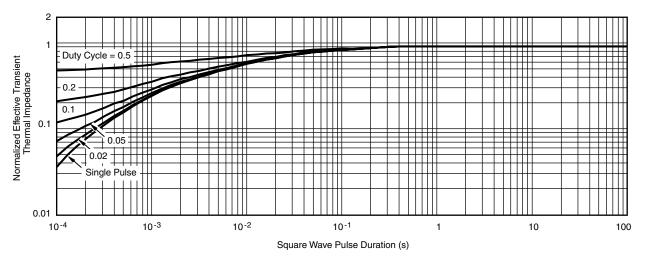


Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix

Document Number: 62664

## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

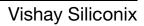


#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

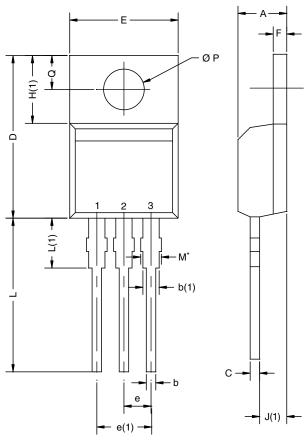
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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## **TO-220AB**



- 6	e(1) <del>-</del>	
		D2

	MILLIM	IETERS	INC	HES		
DIM.	MIN.	MAX.	MIN.	MAX.		
А	4.25	4.65	0.167	0.183		
b	0.69	1.01	0.027	0.040		
b(1)	1.20	1.73	0.047	0.068		
С	0.36	0.61	0.014	0.024		
D	14.85	15.49	0.585	0.610		
D2	12.19	12.70	0.480	0.500		
E	10.04	10.51	0.395	0.414		
е	2.41	2.67	0.095	0.105		
e(1)	4.88	5.28	0.192	0.208		
F	1.14	1.40	0.045	0.055		
H(1)	6.09	6.48	0.240	0.255		
J(1)	2.41	2.92	0.095	0.115		
L	13.35	14.02	0.526	0.552		
L(1)	3.32	3.82	0.131	0.150		
ØΡ	3.54	3.94	0.139	0.155		
Q	2.60	3.00	0.102	0.118		
ECN: T14-0413-Rev. P, 16-Jun-14 DWG: 5471						

#### Note

 $<sup>^{\</sup>star}$  M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM



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